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	Application No.	Applicant(s)	•
Notice of Allowability	09/579,402	KO, KEI-YU	
	Examiner	Art Unit	
	Eugene Lee	2815	
The MAILING DATE of this communication appe All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT Ri- of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in this or other appropriate communicat GHTS. This application is subject	application. If not included ion will be mailed in due cour	se. THIS
1. A This communication is responsive to 10/21/04.			
2. $\boxtimes$ The allowed claim(s) is/are <u>1-9 and 11-30</u> .		•	
3. $igotimes$ The drawings filed on <u>19 April 2001</u> are accepted by the Ex	caminer.		
4. Acknowledgment is made of a claim for foreign priority un a) All b) Some* c) None of the:  1. Certified copies of the priority documents have 2. Certified copies of the priority documents have 3. Copies of the certified copies of the priority documents have International Bureau (PCT Rule 17.2(a)).  * Certified copies not received:  Applicant has THREE MONTHS FROM THE "MAILING DATE" on the other has THREE MONTHS FROM THE "MAILING DATE" on the other has THREE MONTH STAND IS NOT EXTENDABLE.  5. A SUBSTITUTE OATH OR DECLARATION must be submitived in the submitive of the other has a proper of the priority documents and the submitive of the other has a proper of the priority documents and the submitive of the priority documents of the priority documents and the submitive of the priority documents and the submitive of the priority documents of the priority documents have a public of the priority documents of the priority documents and the submitive of the priority documents of the priority documents have a public or a priority document submitive or a priority document of the priority documents and the priority docu	been received.  been received in Application No. cuments have been received in the of this communication to file a rep ENT of this application.  itted. Note the attached EXAMINI es reason(s) why the oath or deci- t be submitted. on's Patent Drawing Review ( PT s Amendment / Comment or in the 84(c)) should be written on the dra ne header according to 37 CFR 1.12 sit of BIOLOGICAL MATERIA	is national stage application in the stage application is deficient.  CO-948) attached in the front (not the backet).  L must be submitted. Note	ments CE OF
Attachment(s)  1. ☐ Notice of References Cited (PTO-892)  2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948)  3. ☐ Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date  4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material	6. ☐ Interview Summa Paper No./Mail I 8), 7. ☐ Examiner's Ame	Date	

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## **DETAILED ACTION**

## Allowable Subject Matter

1. Claims 1 thru 9, and 11 thru 30 are allowed. The following is an examiner's statement of reasons for allowance: The references of record, either singularly or in combination, do not teach or suggest at least "a gate stack structure situated over a semiconductor material layer, said gate stack structure comprising: a contact plug having a base in contact with said semiconductor material layer, said contact plug comprising a second conductive material, said contact plug having a top and a lateral wall, wherein the second conductive material physically contacts the semiconductor material layer; wherein a conductive layer is disposed along said lateral wall along the second conductive material and with said second conductive material comprises a part of said contact plug" (claims 1-8, 21, and 22).

Regarding claims 9, 23, and 24, the references of record, either singularly or in combination, do not teach or suggest at least "a gate stack structure situated over a monocrystalline silicon layer, said gate stack structure comprising: a contact plug having a base in contact with said semiconductor material layer, said contact plug comprising a second conductive material, said contact plug having a top and a lateral wall, wherein the second conductive material physically contacts the semiconductor material layer; wherein a conductive layer is disposed along said lateral wall along the second conductive material and with said second conductive material comprises a part of said contact plug."

Regarding claims 11-18, 25, and 26, the references of record, either singularly or in combination, do not teach or suggest at least "a gate structure comprising: a pair of gate stacks situated over a semiconductor material layer, each said gate stack comprising: a contact plug

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having a base in contact with said semiconductor material layer, said contact plug comprising a second conductive material, said contact plug having a top and a lateral wall, wherein the second conductive material physically contacts the semiconductor material layer; wherein a conductive layer is disposed along said lateral wall along the second conductive material and with said second conductive material comprises a part of said contact plug."

Regarding claims 19, 27, and 28, the references of record, either singularly or in combination, do not teach or suggest at least "a gate stack structure comprising: a pair of gate stacks situated over a monocrystalline silicon layer, each said gate stack comprising: a contact plug having a base in contact with said monocrystalline silicon layer, said contact plug comprising a second conductive material, said contact plug having a top and a lateral wall, wherein the second conductive material physically contacts the semiconductor material layer; wherein a conductive layer is disposed along said lateral wall along the second conductive material and with said second conductive material comprises a part of said contact plug."

Regarding claims 20, 29, and 30, the references of record, either singularly or in combination, do not teach or suggest at least "a gate structure comprising: a pair of gate stacks situated over a monocrystalline silicon layer, each said gate stack comprising: a contact plug having a base in contact with said monocrystalline silicon layer, said contact plug comprising a second conductive material, said contact plug having a top and a lateral wall, wherein the second conductive material physically contacts the semiconductor material layer; wherein a conductive layer is disposed along said lateral wall along the second conductive material and with said second conductive material comprises a part of said contact plug."

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Any comments considered necessary by applicant must be submitted no later than the

payment of the issue fee and, to avoid processing delays, should preferably accompany the issue

fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for

Allowance."

INFORMATION ON HOW TO CONTACT THE USPTO

Any inquiry concerning this communication or earlier communications from the

examiner should be directed to Eugene Lee whose telephone number is 571-272-1733. The

examiner can normally be reached on M-F 8-5.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, Tom Thomas can be reached on 571-272-1664. The fax phone number for the

organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent

Application Information Retrieval (PAIR) system. Status information for published applications

may be obtained from either Private PAIR or Public PAIR. Status information for unpublished

applications is available through Private PAIR only. For more information about the PAIR

system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR

system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Eugene Lee January 18, 2005